

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
an insulating film comprising silicon oxide on an insulating surface,
wherein the insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less
and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less which are detected by second ion mass
spectroscopy.
2. A device according to claim 1, wherein the halogen is chlorine.
3. A device according to claim 1, wherein the halogen is fluorine.
4. A device according to claim 1,
wherein the insulating film includes carbon at a concentration of $1 \times 10^{18} \text{ cm}^{-3}$ or less
which is detected by the second ion mass spectroscopy.
5. A device according to claim 1,
wherein the insulating film includes halogen at a concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or
more which is detected by the second ion mass spectroscopy.
6. A device according to claim 1,
wherein the insulating film is a gate insulating film.
7. A device according to claim 1,
wherein the insulating film is an insulating film in a thin film transistor.
8. A device according to claim 1,
wherein the insulating film covers an even surface over a glass substrate.
9. A device according to claim 1,
wherein the insulating film is formed by plasma chemical vapor deposition using an
organic silane.
10. A device according to claim 9,
wherein the organic silane comprises at least a material selected from the group
consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

11. A semiconductor device comprising:
 a crystalline semiconductor island on an insulating surface; and
 an insulating film including silicon oxide to cover the crystalline semiconductor island,
 wherein the insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less
 and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.
12. A device according to claim 11,
 wherein the concentrations of halogen and carbon are detected by secondary ion
 mass spectroscopy.
13. A device according to claim 11, wherein the halogen is
 chlorine.
14. A device according to claim 11, wherein the halogen is fluorine.
15. A device according to claim 11,
 wherein the insulating film includes carbon at a concentration of $1 \times 10^{18} \text{ cm}^{-3}$ or less.
16. A device according to claim 11,
 wherein the insulating film includes halogen at a concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or
 more.
17. A device according to claim 11,
 wherein the insulating film is formed by plasma chemical vapor deposition using an
 organic silane.
18. A device according to claim 17,
 wherein the organic silane comprises at least a material selected from the group
 consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.
19. A semiconductor device including at least a thin film transistor comprising:
 a crystalline semiconductor island on an insulating surface;
 a silicon oxide film over the crystalline semiconductor island; and
 a conductive film including at least one of aluminum, titanium, and titanium nitride,
 said conductive film being formed on the silicon oxide film,
 wherein the silicon oxide film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or
 less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

20. A device according to claim 19,
wherein the concentrations of halogen and carbon are detected by secondary ion
mass spectroscopy.

21. A device according to claim 19, wherein the halogen is chlorine.

22. A device according to claim 19, wherein the halogen is fluorine.

23. A device according to claim 19,
wherein the silicon oxide film includes carbon at a concentration of $1 \times 10^{18} \text{ cm}^{-3}$ or
less.

24. A device according to claim 19,
wherein the silicon oxide film includes halogen at a concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or
more.

25. A device according to claim 19,
wherein the silicon oxide film is formed by plasma chemical vapor deposition using
an organic silane.

26. A device according to claim 17,
wherein the organic silane comprises at least a material selected from the group
consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.

27. A semiconductor device including at least a thin film transistor comprising:
a crystalline semiconductor island on an insulating surface;
a gate insulating film including silicon oxide on the crystalline semiconductor island;
and
a gate electrode on the gate insulating film,
wherein the gate insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$
or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

28. A device according to claim 27,
wherein the concentrations of halogen and carbon are detected by secondary ion
mass spectroscopy.

29. A device according to claim 27, wherein the halogen is chlorine.

30. A device according to claim 27, wherein the halogen is fluorine.

31. A device according to claim 27,
wherein the gate insulating film includes carbon at a concentration of $1 \times 10^{18} \text{ cm}^{-3}$ or less.

32. A device according to claim 27,
wherein the gate insulating film includes halogen at a concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or more.

33. A device according to claim 27,
wherein the gate insulating film is formed by plasma chemical vapor deposition using an organic silane.

34. A device according to claim 33,
wherein the organic silane comprises at least a material selected from the group consisting of $\text{Si}(\text{OC}_2\text{H}_5)_4$, $\text{Si}_2\text{O}(\text{OC}_2\text{H}_5)_6$, $\text{Si}_3\text{O}_2(\text{OC}_2\text{H}_5)_8$, $\text{Si}_4\text{O}_3(\text{OC}_2\text{H}_5)_{10}$ and $\text{Si}_5\text{O}_4(\text{OC}_2\text{H}_5)_{12}$.